AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An integrated circuit device comprising:

~~a semiconductor~~ an amplification ~~element~~ transistor supplied with a voltage from a first power source; ~~and~~

a bias circuit including a bias generating circuit for ~~applying~~ generating a base bias voltage applied to the ~~semiconductor~~ amplification ~~element~~ transistor, wherein

the bias circuit is supplied with a second voltage from a second power source, and

the second power source is connected to the first power source via a diode~~,~~ ~~and~~ so that idle current of the ~~semiconductor~~ amplification ~~element change~~ transistor changes in response to a change of the voltage supplied by the first power source to the ~~semiconductor~~ amplification ~~element~~ transistor; and

a temperature compensation circuit temperature compensating the bias generating circuit.

Claims 2-4 (Cancelled).

5. (New) The integrated circuit device according to claim 1, wherein the temperature compensation circuit includes two diode-connected transistors connected in series and coupled to a third power source, the diode-connected transistors providing a temperature compensating signal to the generating bias circuit.

6. (New) An integrated circuit device comprising:

an amplification transistor supplied with a voltage from a first power source; and

a bias circuit for applying a bias voltage to the amplification transistor, wherein the bias circuit includes an emitter-follower circuit comprising

a first biasing transistor supplied with a second voltage from a second power source, and

a second biasing transistor connected in parallel with the first biasing transistor and having a collector coupled to the first power source so that idle current of the amplification transistor changes in response to a change of the voltage supplied by the first power source to the amplification transistor.

7. (New) The integrated circuit device according to claim 6 including a temperature compensation circuit temperature compensating the bias circuit.

8. (New) The integrated circuit device according to claim 7, wherein the temperature compensation circuit includes two diode-connected transistors connected in series and coupled to a third power source, the diode-connected transistors providing a temperature compensating signal to the first and second biasing transistors.

9. (New) The integrated circuit device according to claim 7, wherein the temperature compensation circuit includes a current mirror circuit, supplied with a third voltage from a third power source and coupled to the second power source, for supplying a temperature-compensating signal to the first and second biasing transistors.

10. (New) An integrated circuit device comprising:

an amplification transistor supplied with a voltage from a first power source; and

a bias circuit for applying a bias voltage to the amplification transistor, wherein the bias circuit comprises

an emitter follower circuit including a biasing transistor supplied with a second voltage from a second power source through a first diode, and

a second diode connecting the first power source to the biasing transistor, the first and second diodes being connected in like polarity to the biasing transistor so that idle current of the amplification transistor changes in response to a change of the voltage supplied by the first power source to the amplification transistor.

11. (New) The integrated circuit device according to claim 10 including a temperature compensation circuit temperature compensating of the bias circuit.

12. (New) The integrated circuit device according to claim 11, wherein the temperature compensation circuit includes two diode-connected transistors connected in series and coupled to a third power source, the diode-connected transistors providing a temperature compensating signal to the biasing transistor.

This listing of claims replaces all prior versions, and listings, of claims in the application.